In$_2$O$_3$ doped with SnO$_2$ (10% by weight) (Evaporated)

- MHA etch based on InP etching
- Cyclic etching to combat polymer build-up:
  - CH$_4$/H$_2$/Ar (4/22/4 sccm) 50mT 500V 5min
  - O$_2$ (20 sccm) 50mT 200V 3min
- Bulk etch rate ~ 35nm/min
- Rate depends strongly on ITO quality
- SiO$_2$ or SiO$_2$/Cr hard masks
- Example: ITO PhC with $a = 224$nm

Elizabeth Rollings

ITO PhC with SiO$_2$ hard mask